

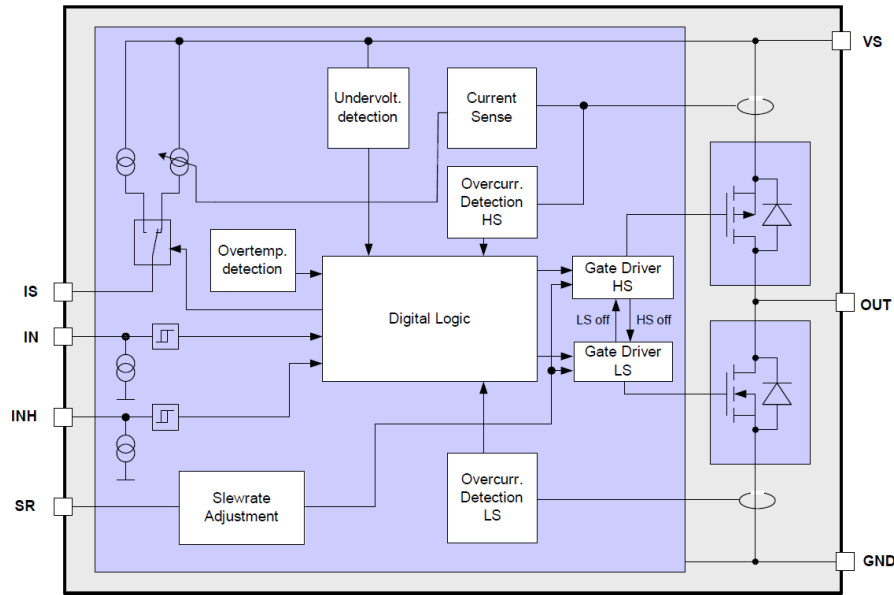
Motor driver for Arduino

IFX007T

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2019.3.23

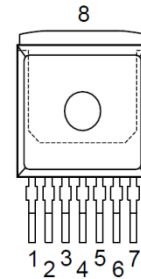


High Current PN Half Bridge with Integrated Driver IFX007T



Summary of features:

- Path resistance of max. 12.8 mΩ @ 25°C (typ. 10.0 mΩ @ 25°C)
High side: max. 6.5 mΩ @ 25°C (typ. 5.3 mΩ @ 25°C)
Low side: max. 6.3 mΩ @ 25°C (typ. 4.7mΩ @ 25°C)
- Enhanced switching speed for reduced switching losses
- Capable for high PWM frequency combined with active freewheeling
- Current limitation level of 55A min.
- Status flag diagnosis with current sense capability
- Undervoltage shutdown
- Driver circuit with logic level inputs
- Adjustable slew rates for optimized EMI
- Operation up to 40V
- Green Production(RoHS compliant)
- JESD471 Qualified



Pin	Symbol	I/O	Function
1	GND	-	Ground
2	IN	I	Input Defines whether high - or low-side switch is activated
3	INH	I	Inhibit When set to low device goes in sleep mode
4,8	OUT	O	Power output of the bridge
5	SR	I	Slew Rate The slew rate of the power switches can be adjusted by connecting a resistor between SR and GND
6	IS	O	Current Sense and Diagnostics
7	VS	-	Supply

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Supply voltage range for normal operation	$V_{S(nor)}$	8	-	40	V	$T_j \geq 25^\circ\text{C}$	P_4.2.1
		8	-	38	V	$T_j < 25^\circ\text{C}$	
Junction temperature	T_j	-40	-	150	$^\circ\text{C}$	-	P_4.2.2

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
Undervoltage shutdown							
Switch-ON voltage	$V_{UV(ON)}$	–	–	5.0	V	V_S increasing	P_5.3.1
Switch-OFF voltage ¹⁾	$V_{UV(OFF)}$	3.3	–	4.7	V	V_S decreasing, INH = 1	P_5.3.2
ON/OFF hysteresis	$V_{UV(HY)}$	–	0.3	–	V	²⁾	P_5.3.3

NovalithIC™ – Explanation of features

3 Undervoltage shut down:

- > Protects the device at low supply voltages

2 Overtemp. Protection:

- > Fast and precise integrated temperature sensor

1 Logic-Level Input Voltage:

- > Direct connection to 3.3V or 5V μ C = no level-shifter needed

Protection & Diagnosis

4 Integrated Current-Sense:

Savings due to integrated current sense:

- > Current sense amplifier
- > High-current shunt
- > Cooling for a power shunt
- > PCB area for devices and cooling
- > Less pick and place due to decreased BOM

5 Current Limitation:

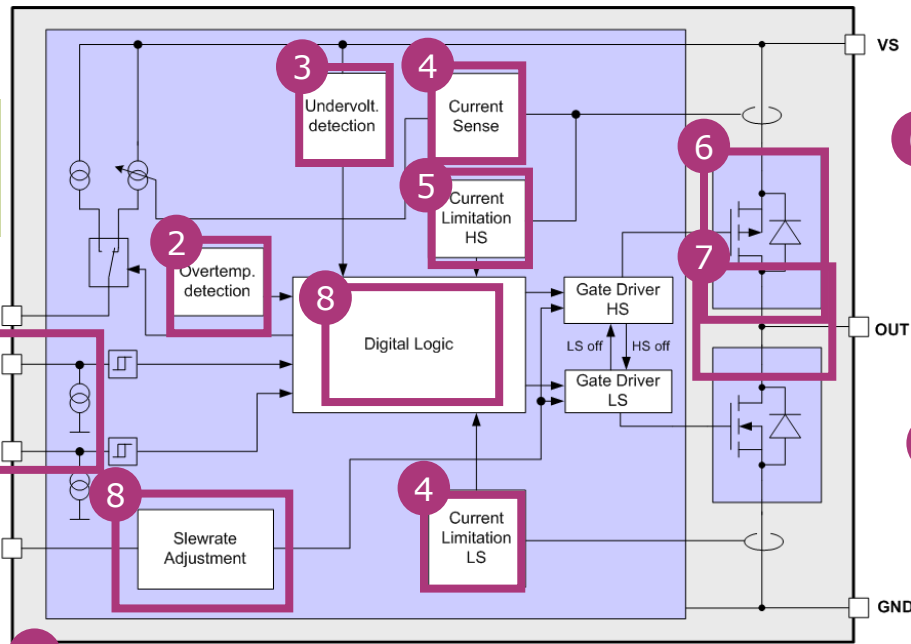
- > Internal current measurement function to detect and protect against overcurrent situations for HS & LS

6 PWM capability:

- > PFET at high-side eliminates use of a charge pump
- > Improves EMC performance and provides unlimited PWM frequency

7 Reduced parasitics:

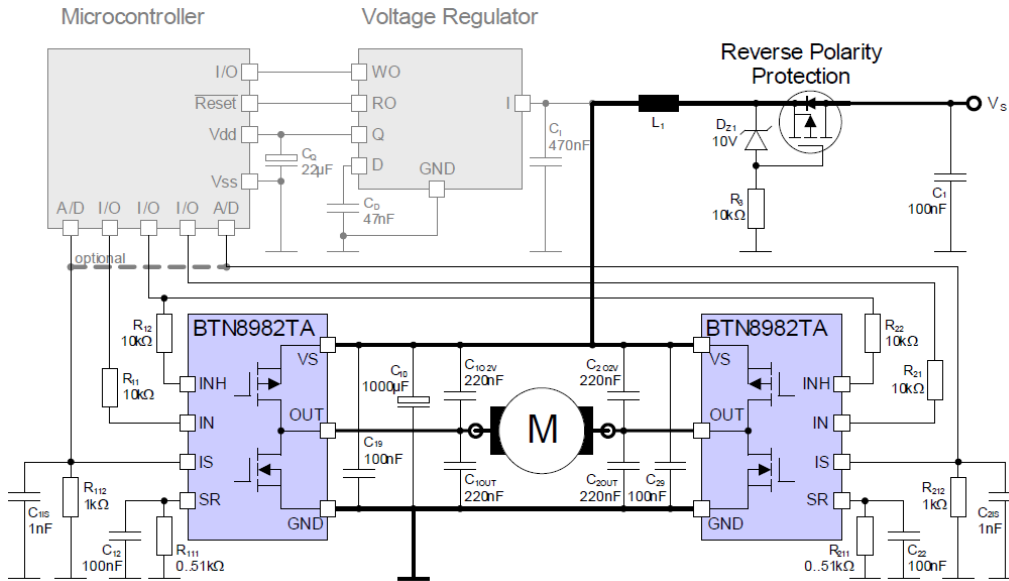
- > Integration of HS and LS switches in one package reduces parasitics (stray inductances) dramatically



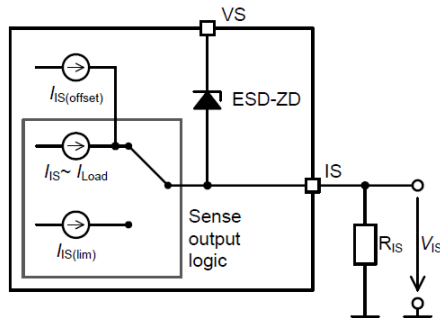
8 Ease-of-Control:

- > Switching speed can be adjusted via an external slew rate resistor, optimizing between EMI and P_{DISS} and automatically adjusting the dead-time

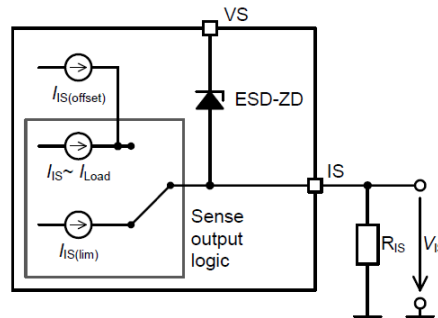
Current sense (IS pin)



Normal operation:
current sense mode



Fault condition:
error flag mode



Device State	Inputs		Outputs			Mode
	INH	IN	HSS	LSS	IS	
Normal Operation	0	X	OFF	OFF	0	Stand-by mode
	1	0	OFF	ON	$I_{IS(offset)}$	LSS active
	1	1	ON	OFF	CS	HSS active
Under-Voltage (UV)	X	X	OFF	OFF	0	UV lockout, reset
Overtemperature (OT) or Short Circuit of HSS or LSS	0	X	OFF	OFF	0	Stand-by mode, reset of latch
Current Limitation Mode/ Overcurrent (OC)	1	X	OFF	OFF	1	Shut-down with latch, error detected
	1	1	OFF	ON	1	Switched mode, error detected ¹⁾
	1	0	ON	OFF	1	Switched mode, error detected ¹⁾

1) Will return to normal operation after t_{CLS} . Error signal is reset after $2 \cdot t_{CLS}$ (see Chapter 5.3.3)

Inputs	Switches	Current Sense / Status Flag IS
0 = Logic LOW	OFF = switched off	$I_{IS(offset)}$ = Current sense - Offset (for conditions see table: Current Sense)
1 = Logic HIGH	ON = switched on	CS = Current sense - high side (for conditions see table: Current Sense)
X = 0 or 1		1 = Logic HIGH (error)

Current Sense

5.4.6	Differential Current Sense ratio in static on-condition $dk_{ILIS} = dI_L / dI_{IS}$	dk_{ILIS}	14	19.5	25	10^3	$R_{IS} = 1 \text{ k}\Omega$ $I_{L1} = 10 \text{ A}$ $I_{L2} = 40 \text{ A}$
5.4.7	Maximum analog Sense Current, Sense Current in fault Condition	$I_{IS(lim)}$	4	5	6.5	mA	$V_S = 13.5 \text{ V}$ $R_{IS} = 1 \text{ k}\Omega$
5.4.8	Isense Leakage current	I_{ISL}	—	—	1	μA	$V_{INH} = 0 \text{ V}$
5.4.9	Isense offset current	$I_{IS(offset)}$	30	170	385	μA	$V_S = 18 \text{ V}$; $V_{INH} = 5 \text{ V}$ $I_{SD(HS)} = 0 \text{ A}$

$$I_{IS} = \frac{1}{dk_{ILIS}} \cdot I_L + I_{IS(offset)}$$

$$I_L = dk_{ILIS} \cdot (I_{IS} - I_{IS(offset)})$$

$$V_{IS} = R_{IS} \cdot I_{IS}$$

Switching Time (SR pin)

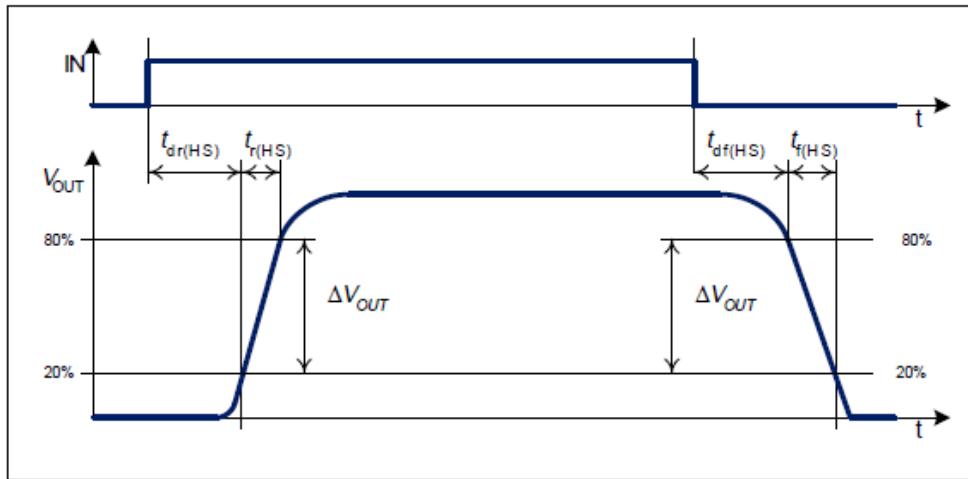


Figure 7 Definition of switching times high side (R_{load} to GND)

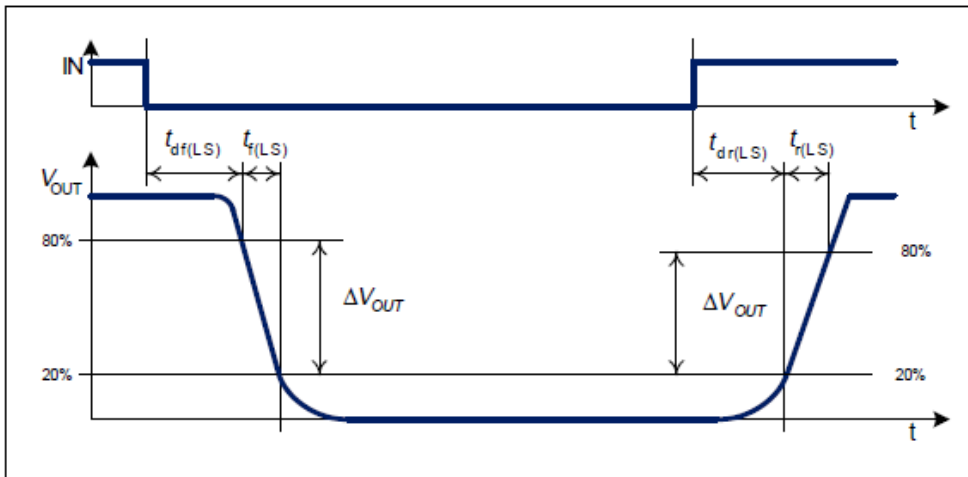


Figure 8 Definition of switching times low side (R_{load} to V_S)

Due to the timing differences for the rising and the falling edge there will be a slight difference between the length of the input pulse and the length of the output pulse. It can be calculated using the following formulas:

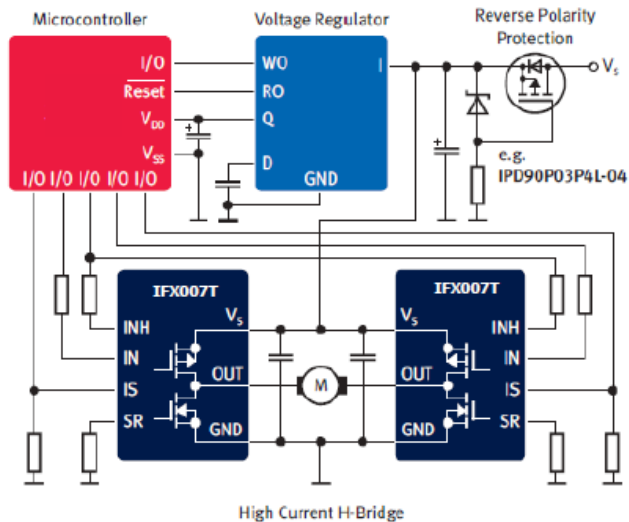
- $\Delta t_{HS} = (t_{dr(HS)} + 0.5 t_{r(HS)}) - (t_{df(HS)} + 0.5 t_{f(HS)})$
- $\Delta t_{LS} = (t_{df(LS)} + 0.5 t_{f(LS)}) - (t_{dr(LS)} + 0.5 t_{r(LS)})$

Parameter	Symbol	Values			Unit	Note or Test Condition	Number
		Min.	Typ.	Max.			
High-side switch dynamic characteristics							
Rise-time of HS	$t_{r(HS)}$	0.05 0.22	0.25 1.3	0.75 4.7	μs	$R_{SR} = 0\ \Omega$ $R_{SR} = 51\ k\Omega$	P_5.2.7
Switch-ON delay time HS	$t_{dr(HS)}$	1.5 2	3.4 15	4.6 31	μs	$R_{SR} = 0\ \Omega$ $R_{SR} = 51\ k\Omega$	P_5.2.8
Fall-time of HS	$t_{f(HS)}$	0.05 0.22	0.25 1.3	0.7 4.5	μs	$R_{SR} = 0\ \Omega$ $R_{SR} = 51\ k\Omega$	P_5.2.9
Switch-OFF delay time HS	$t_{df(HS)}$	0.8 1.1	2.4 9	4.1 21	μs	$R_{SR} = 0\ \Omega$ $R_{SR} = 51\ k\Omega$	P_5.2.10

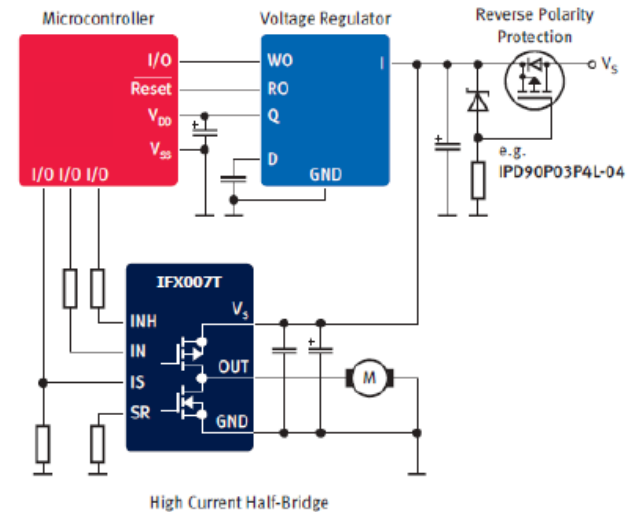
Low-side switch dynamic characteristics							
Rise-time of LS	$t_{r(LS)}$	0.05 0.22	0.25 1.3	0.7 4.5	μs	$R_{SR} = 0 \Omega$ $R_{SR} = 51 k\Omega$	P_5.2.11
Switch-OFF delay time LS	$t_{dr(LS)}$	0.2 1	1.5 7	2.5 16	μs	$R_{SR} = 0 \Omega$ $R_{SR} = 51 k\Omega$	P_5.2.12
Fall-time of LS	$t_{f(LS)}$	0.025 0.18	0.25 1.3	0.7 4.5	μs	$R_{SR} = 0 \Omega$ $R_{SR} = 51 k\Omega$	P_5.2.13
Switch-ON delay time LS	$t_{df(LS)}$	1.6 2.0	4.2 16	5.9 36	μs	$R_{SR} = 0 \Omega$ $R_{SR} = 51 k\Omega$	P_5.2.14

Motor application diagrams

Bi-Directional Motor Application Diagram in H-Bridge Configuration

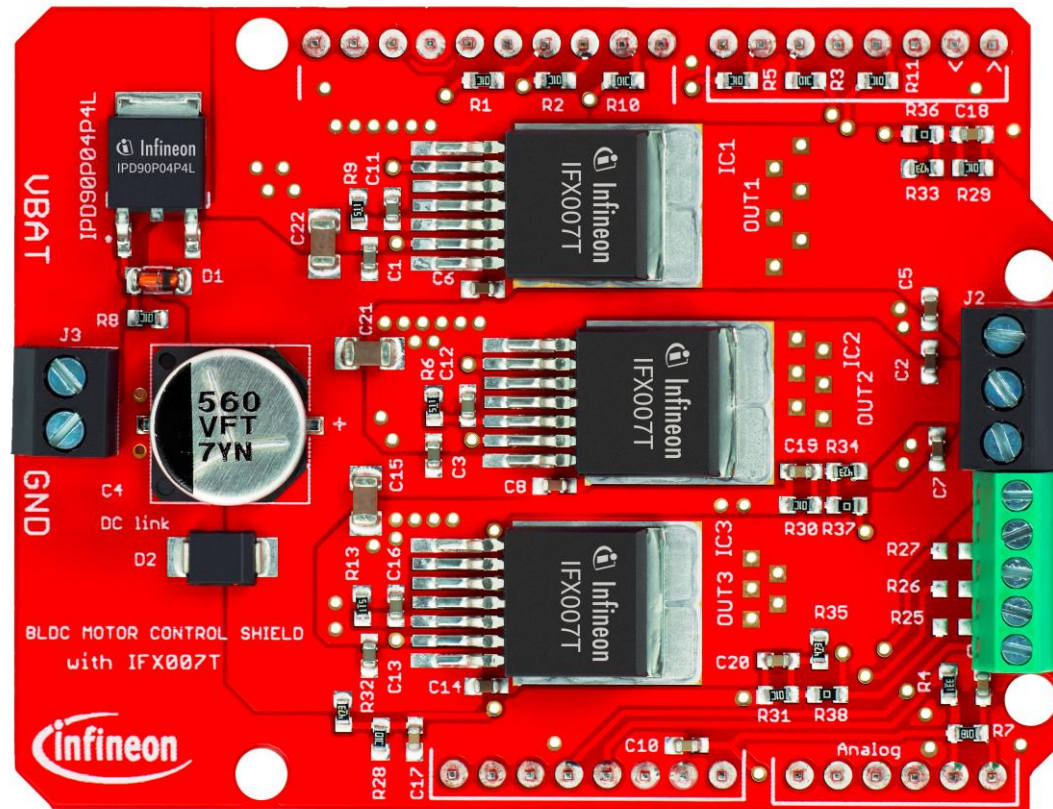


Mono-directional Motor Application Diagram in Half-Bridge Configuration



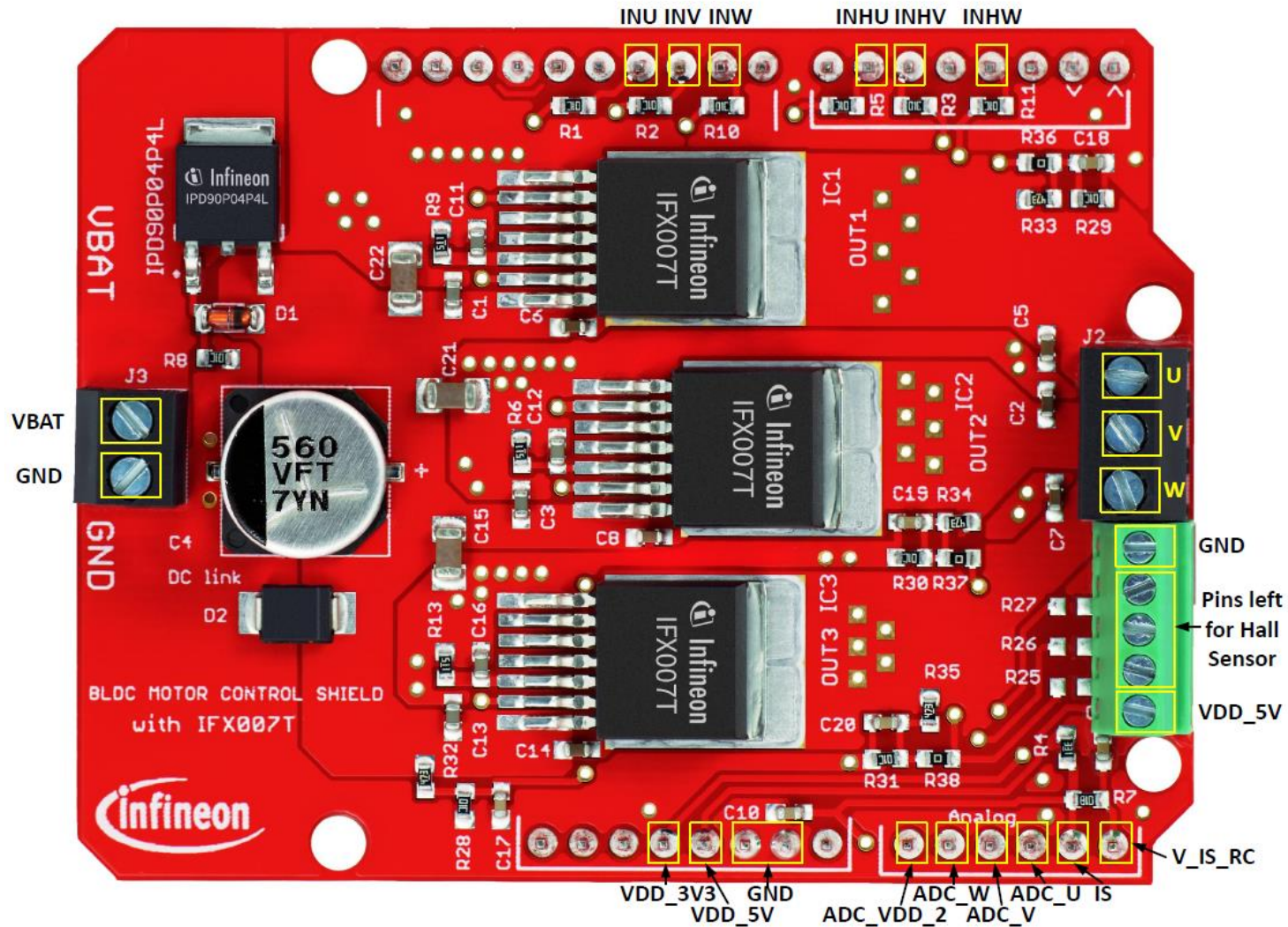
Each is featuring one P-channel high side MOSFET and one N-channel low side MOSFET with an integrated driver IC in one package.
Due to the P-channel high side switch a charge pump is not needed.

On board of the Motor Control Shield are three IFX007T NovalithIC.

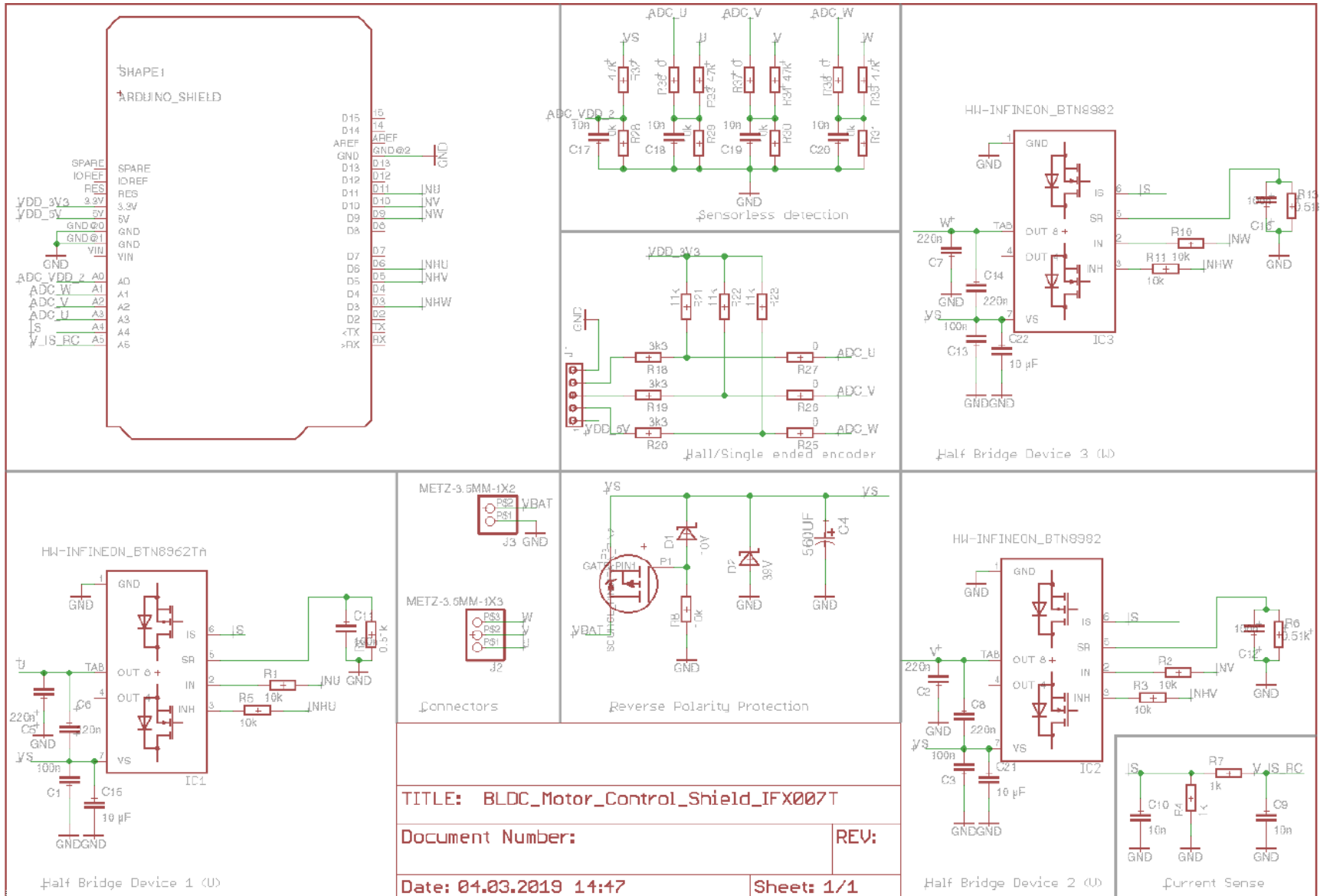


- Each is capable of driving up to 55 A.
- The limited thermal performance of the Shield PCB limits the recommended maximum current to 30 A.

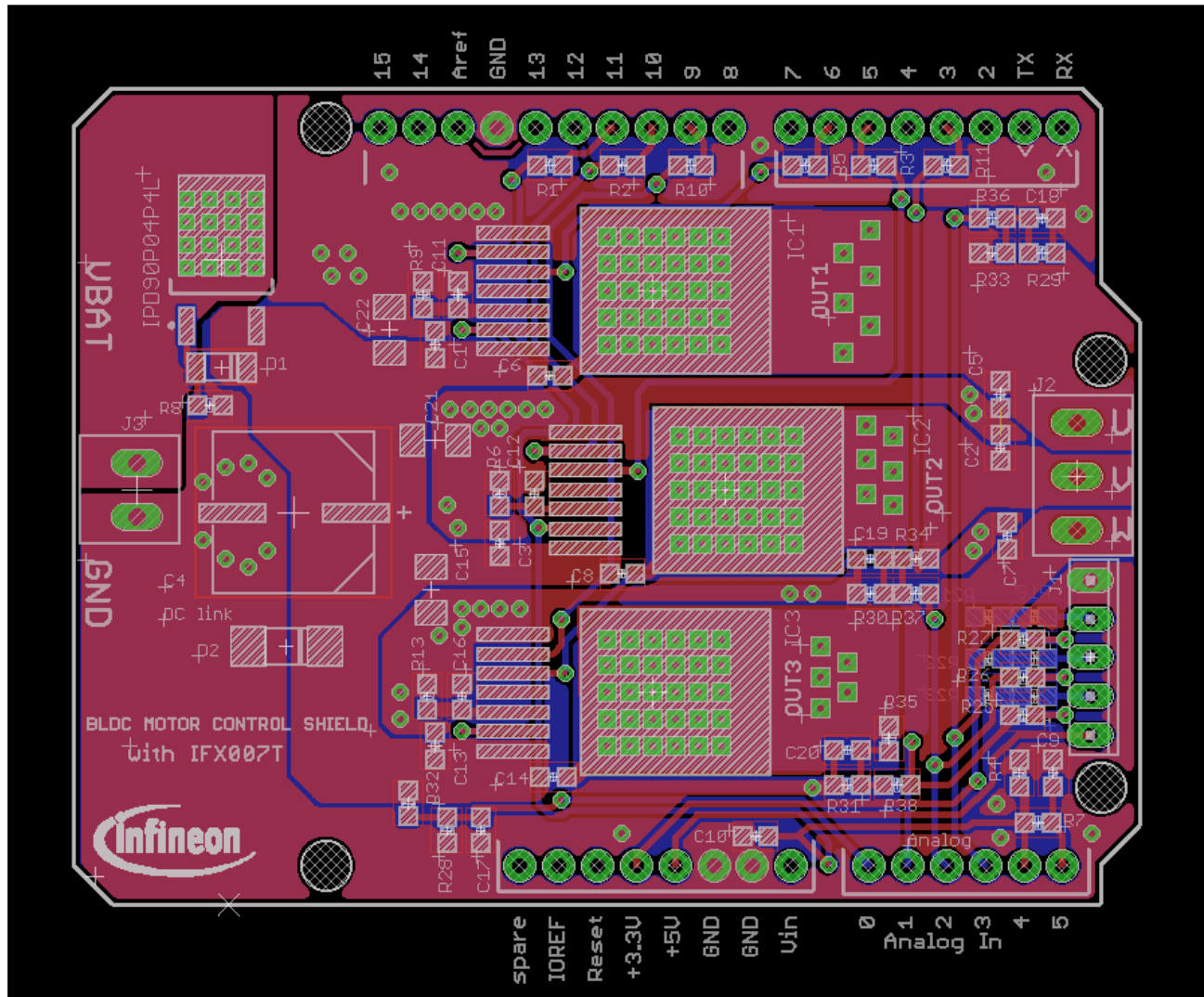
Motor Control Shield



Motor control board schematics



PCB Layout

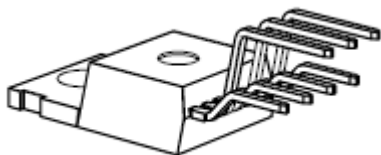


Power supply

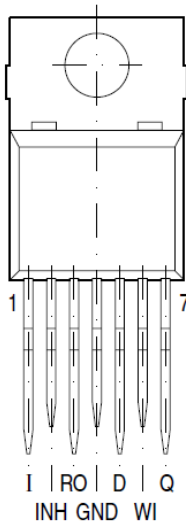
TLE4271-2 (5V 0.5A)

TLE4284 DV50(5V 1A)

(option 1) TLE 4271-2



PG-TO220-7-11



Features

- Output voltage tolerance $\leq \pm 2\%$
- Low-drop voltage
- Integrated overtemperature protection
- Reverse polarity protection
- Input voltage up to 42 V
- Overvoltage protection up to 65 V (≤ 400 ms)
- Short-circuit proof
- Suitable for use in automotive electronics
- Wide temperature range
- Adjustable reset and watchdog time
- Green Product (RoHS compliant)
- AEC Qualified

Table 1 Pin Definitions and Functions

Pin	Symbol	Function
1	I	Input; block to ground directly on the IC with ceramic capacitor.
2	INH	Inhibit
3	RO	Reset Output; the open collector output is connected to the 5 V output via an integrated resistor of 30 k Ω .
4	GND	Ground
5	D	Reset Delay; connect a capacitor to ground for delay time adjustment.
6	WI	Watchdog Input
7	Q	5-V Output; block to ground with 22 μ F capacitor, ESR < 3 Ω .

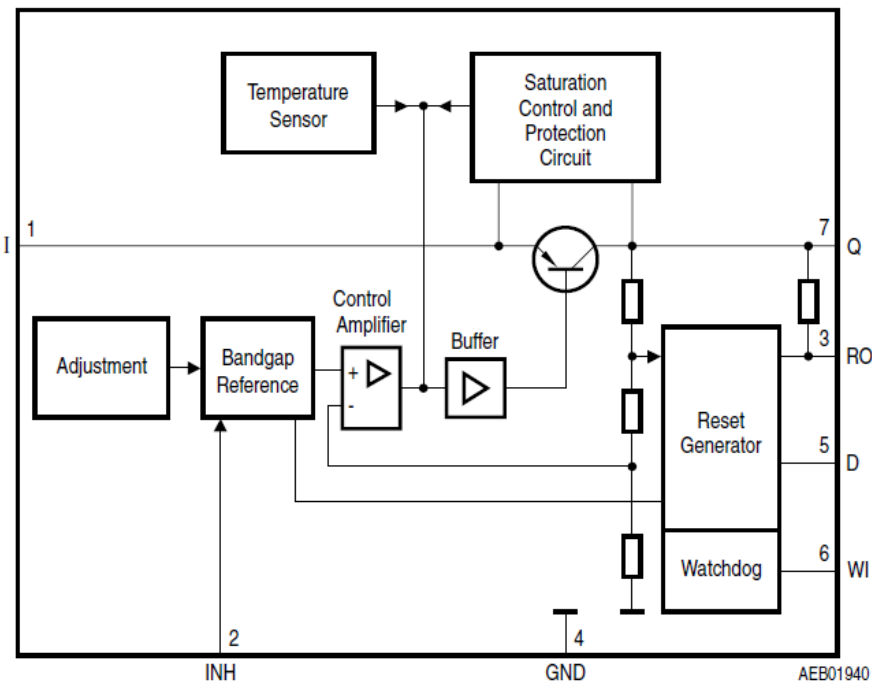


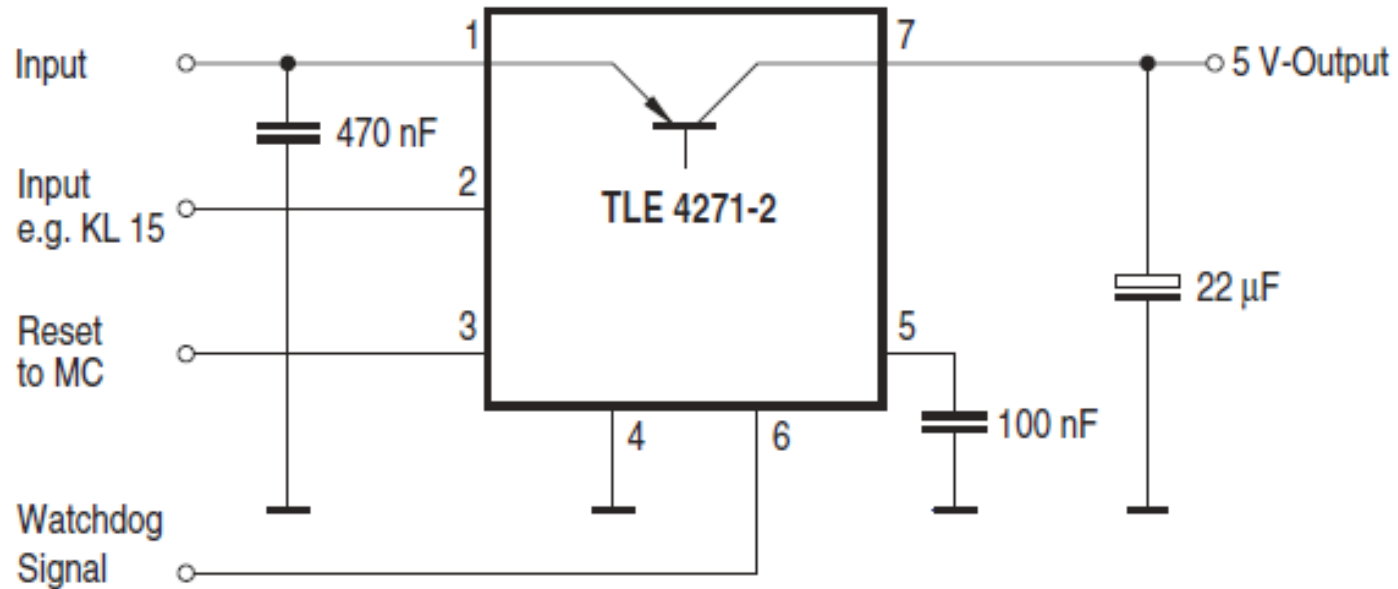
Table 3 Operating Range

Parameter	Symbol	Limit Values		Unit	Notes
		Min.	Max.		
Input voltage	V_I	6	40	V	–
Junction temperature	T_j	-40	150	$^{\circ}$ C	–

$V_I = 13.5$ V; -40 $^{\circ}$ C $\leq T_j \leq 125$ $^{\circ}$ C; $V_{INH} > V_{U,INH}$ (unless otherwise specified)

Parameter	Symbol	Limit Values			Unit	Test Condition
		Min.	Typ.	Max.		
Output voltage	V_Q	4.90	5.00	5.10	V	$5 \text{ mA} \leq I_Q \leq 550 \text{ mA}$; $6 \text{ V} \leq V_I \leq 26 \text{ V}$
Output voltage	V_Q	4.90	5.00	5.10	V	$26 \text{ V} \leq V_I \leq 36 \text{ V}$; $I_Q \leq 300 \text{ mA}$
Output current limiting	I_{Qmax}	650	800	–	mA	$V_Q = 0$ V

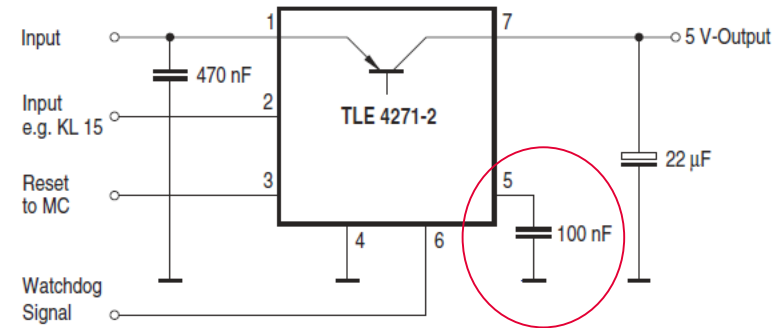
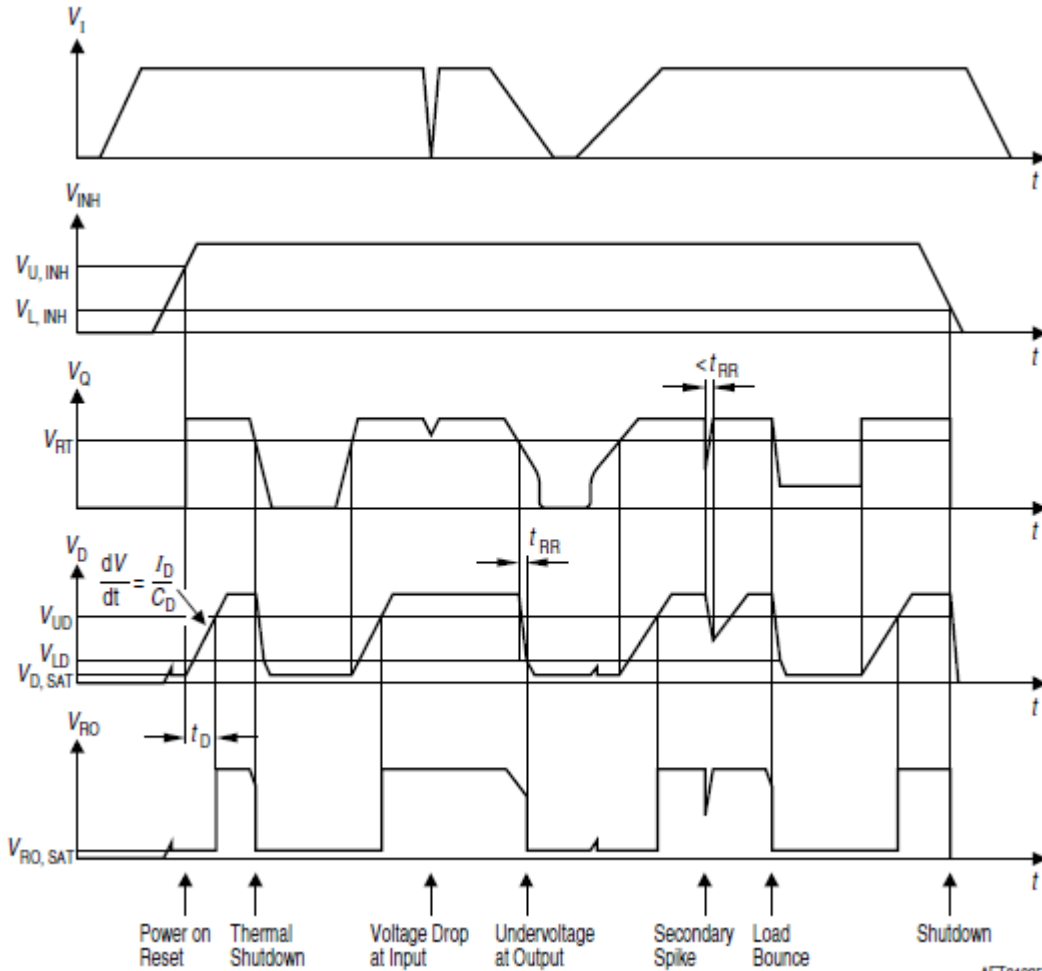
TLE4271-2 Circuit



Thermal Resistance

Junction ambient	R_{thja}	–	65	K/W	–
		–	70	K/W	PG-TO263-7-1
Junction case	R_{thjc} Z_{thjc}	–	3	K/W	–
		–	2	K/W	$t < 1 \text{ ms}$

Reset timing setting



$$t_D = C_D \times \Delta V / I_D$$

Definitions:

- C_D = delay capacitor
- t_D = reset delay time
- I_D = charge current, typical 14 μ A
- $\Delta V = V_{UD}$, typical 1.8 V
- V_{UD} = upper delay timing threshold at C_D for reset delay time

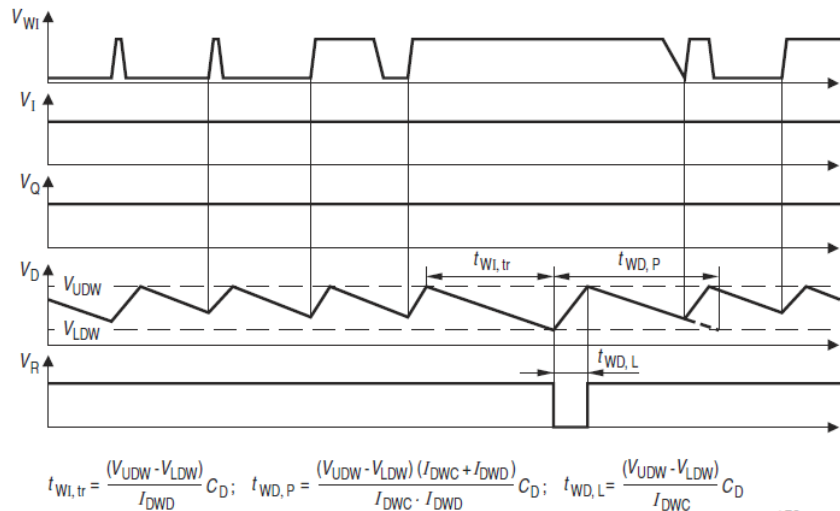
$V_I = 13.5$ V; -40 °C $\leq T_j \leq 125$ °C; $V_{INH} > V_{U,INH}$ (unless otherwise specified)

Parameter	Symbol	Limit Values			Unit	Test Condition
		Min.	Typ.	Max.		
Reset Generator						
Switching threshold	V_{RT}	4.5	4.65	4.8	V	–
Reset high voltage	V_{ROH}	4.5	–	–	V	–
Saturation voltage	$V_{RO,SAT}$	–	60	–	mV	$R_{intern} = 30\text{ k}\Omega$; $1.0\text{ V} \leq V_Q \leq 4.5\text{ V}$
Saturation voltage	$V_{RO,SAT}$	–	200	400	mV	$I_R = 3\text{ mA}^{(2)}$; $V_Q = 4.4\text{ V}$
Reset pull-up	R	18	30	46	k Ω	internally connected to Q
Lower reset timing threshold	V_{LD}	0.2	0.45	0.8	V	$V_Q < V_{RT}$
Charge current	I_D	8	14	25	μA	$V_D = 1.0\text{ V}$
Upper timing threshold	V_{UD}	1.4	1.8	2.3	V	–
Delay time	t_D	8	13	18	ms	$C_D = 100\text{ nF}$
Reset reaction time	t_{RR}	–	–	3	μs	$C_D = 100\text{ nF}$

$$t_{RR} \approx 20 \text{ s/F} \times C_d$$

Watchdog Timing setting

› Watchdog setting with cap value.

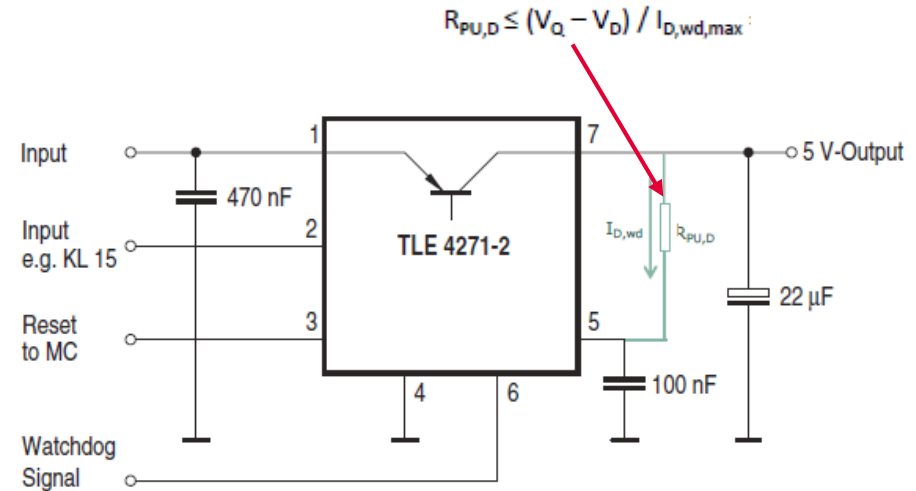


Watchdog

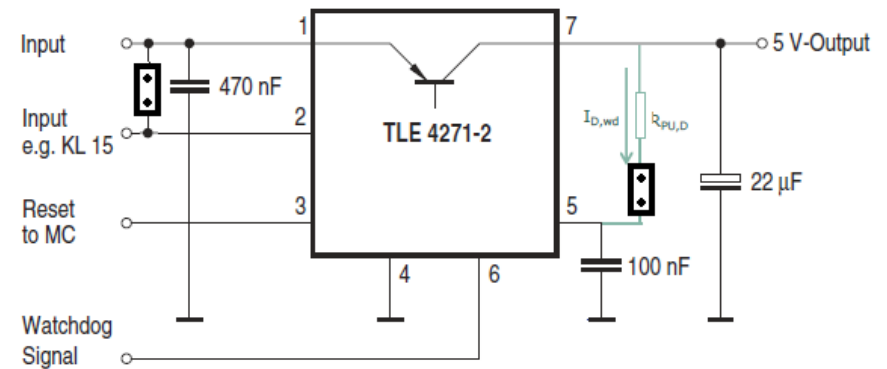
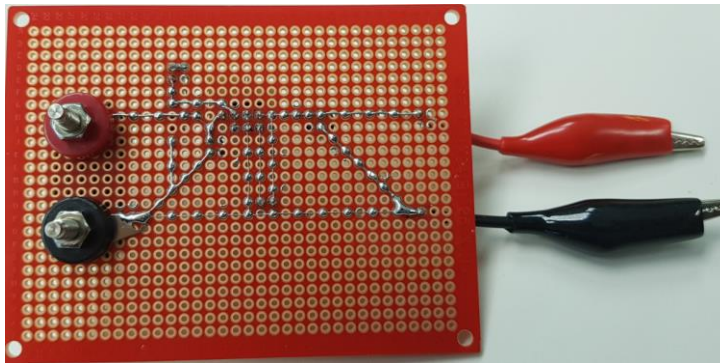
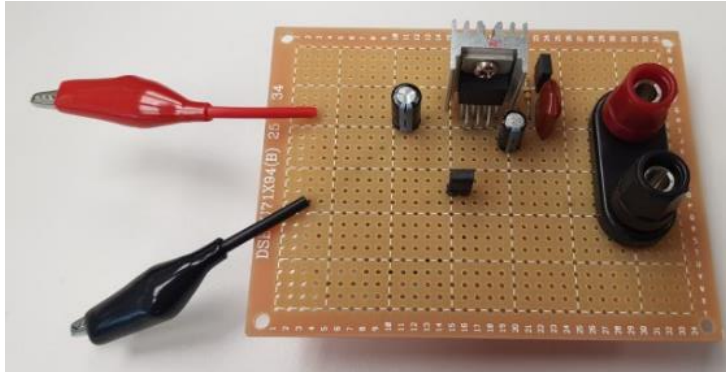
Upper watchdog switching threshold	V_{UDW}	1.4	1.8	2.3	V	–
Lower watchdog switching threshold	V_{LDW}	0.2	0.45	0.8	V	–
Discharge current	I_{DWD}	1.5	2.7	3.5	μA	$V_D = 1 V$
Charge current	I_{DWC}	8	14	25	μA	$V_D = 1 V$
Watchdog period	$t_{WD, P}$	40	55	80	ms	$C_D = 100 nF$
Watchdog trigger time	$t_{WI, tr}$	30	45	66	ms	$C_D = 100 nF$ see diagram
Watchdog pulse slew rate	V_{WI}	5	–	–	V/ μs	from 20% to 80% V_Q

› Watchdog disable

- › Connecting the D pin to the output Q via a pull-up resistor to compensate the discharge current of the watchdog.



TLE4271-2 test board assembly example.



Thermal considerations

How to calculate a heat sink?

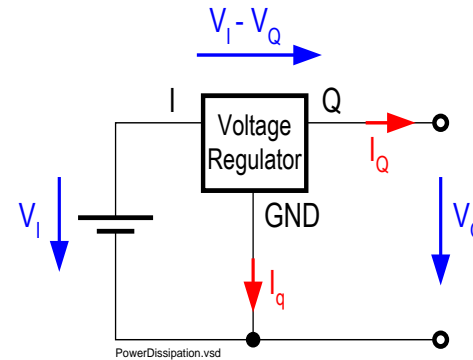
Which Power must be dissipated?

$$P_V = (V_I - V_Q) * I_Q + V_I * I_q$$

$$P_V = (V_{in} - V_{out}) * I_Q$$

$$P_V = (8V - 5V) * 0,5A$$

$$P_V = 1.5W$$



Which Rthj-a would be needed to dissipate this Power losses?

$$T_{junction} = (R_{thJA} * P_V) + T_{ambient}$$

$$R_{thj-a_need} = (T_{jmax} - T_a) / P_V$$

$$R_{thj-a_need} = (150 - 25^\circ C) / 1.5W$$

$$R_{thj-a_need} = 83.33K/W$$

As a result, the PCB design must ensure a thermal resistance RthJA lower than 29,5K/W.

Referring to the thermal resistance table of the TLE4271-2G:

Thermal Resistance

Junction ambient	R_{thja}	–	65	K/W	–
		–	70	K/W	PG-TO263-7-1
Junction case	R_{thjc} Z_{thjc}	–	3	K/W	–
		–	2	K/W	$t < 1 \text{ ms}$

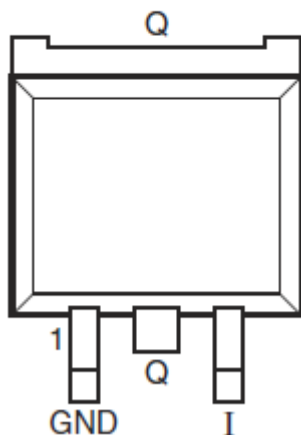
Only a FR4 2s2p board could be used.

(option 2) TLE4284 DV50



PG-TO-252-3

Fixed Output Voltage Version



Features

- Adjustable output voltage or 1.5V, 1.8V, 2.6V, 3.3 V, 5.0V output voltage
- 1.0 A output current
- Low dropout voltage, typ. 1 V
- Short circuit protection
- Overtemperature protection
- Wide operating range up to 40 V
- Wide temperature range of $T_j = -40$ to 150 °C
- Suitable for use in automotive electronics
- Green Product (RoHS compliant)
- AEC Qualified

Table 1 Pin Definitions and Functions Fixed Output Voltage Versions

Pin No.	Symbol	Function
1	GND	Ground
2, Tab	Q	Output; Connect output pin to GND via a capacitor $C_O \geq 10 \mu\text{F}$ with $\text{ESR} \leq 10 \Omega$. Connect to heatsink area.
3	I	Input

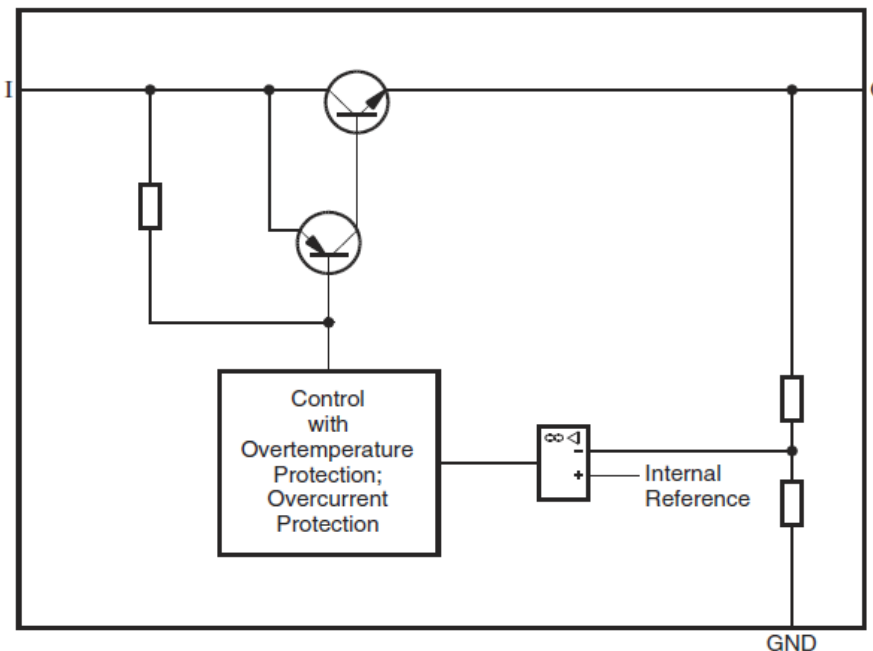
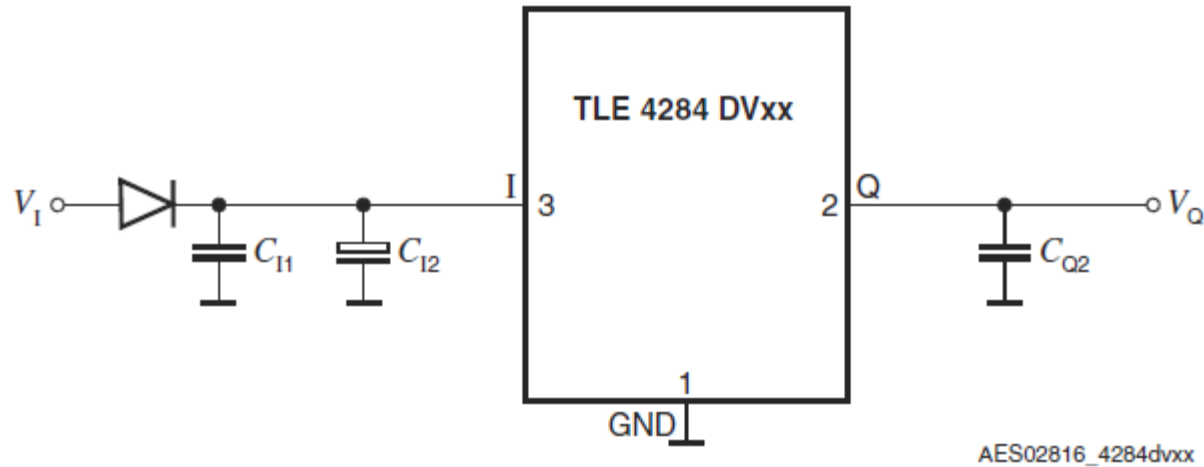


Table 10 Electrical Characteristics TLE 4284 DV50 (5.0 V fixed output voltage)
 -40 °C < T_j < 150 °C; $V_I = 13.5$ V, $I_Q = 10$ mA; unless otherwise specified

Parameter	Symbol	Limit Values			Unit	Measuring Conditions
		min.	typ.	max.		
Output voltage	V_O	4.85	5.00	5.15	V	$10 \text{ mA} \leq I_O \leq 1000 \text{ mA}$; $6.4 \text{ V} \leq V_I \leq 16 \text{ V}$
		–	5.00	–	V	$10 \text{ mA} \leq I_O \leq 1000 \text{ mA}$; $16 \text{ V} \leq V_I \leq 40 \text{ V}^{(1)}$
Current limit	$I_{Q\text{max}}$	1000	–	2200	mA	$V_I - V_O < 18 \text{ V}$; $V_O = V_{\text{nom}} - 100 \text{ mV}$
		50	200	–	mA	$V_I = 40 \text{ V}$; $V_O = V_{\text{nom}} - 100 \text{ mV}$ $T_j = 25$ °C

TLE4284DV50 Circuit



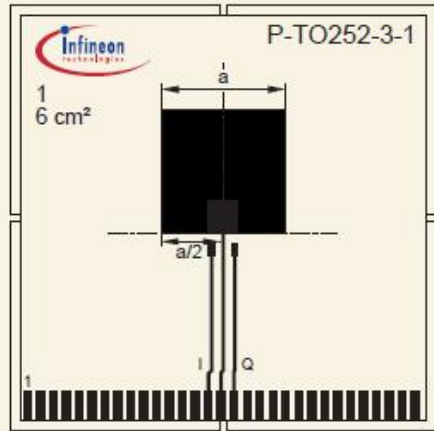
Thermal Resistance

Junction ambient	R_{thja}	–	144	K/W	PG-TO252-3-11 footprint only ¹⁾
		–	78	K/W	PG-TO252-3-11 300 mm ² heat sink area ¹⁾
		–	54	K/W	PG-TO252-3-11 600 mm ² heat sink area ¹⁾
Junction case	R_{thjc}	–	4	K/W	–

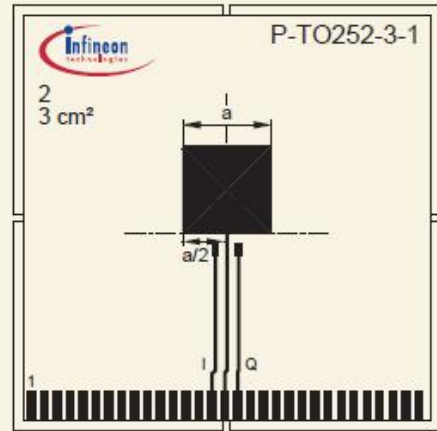
1) FR4, 80 x 80 x 1.5mm², 35µm Cu, 5µm Sn, horizontal position, zero airflow

TO252

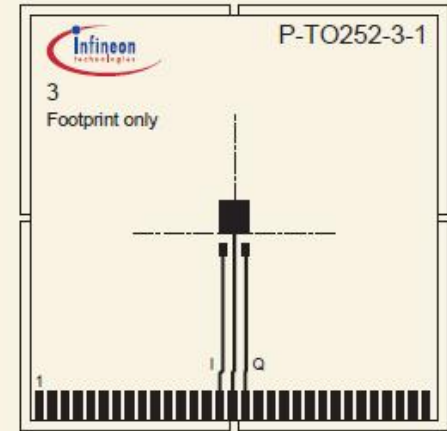
Application-Boards for R_{th} - Measurement



FR4; 80x80x1.5 mm; 35 μ Cu, 5 μ Sn
A = 600 mm²; a = 24.49 mm



FR4; 80x80x1.5 mm; 35 μ Cu, 5 μ Sn
A = 300 mm²; a = 17.32 mm

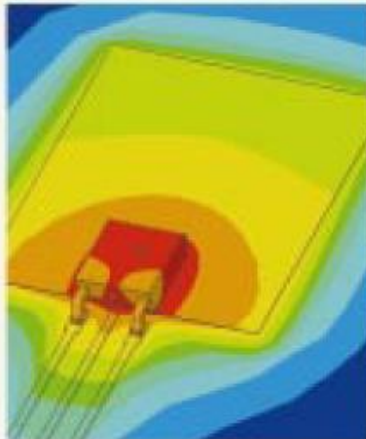


FR4; 80x80x1.5 mm; 35 μ Cu, 5 μ Sn
Footprint only

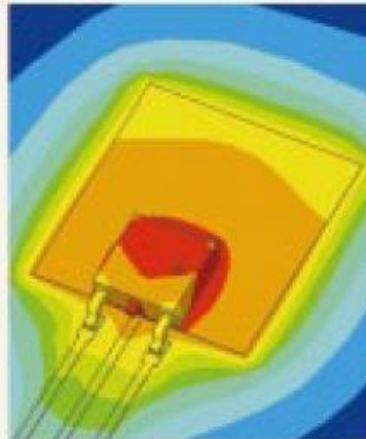
PC-Board

FEM Simulation (chip area ≥ 2 mm²; $P_v = 1$ W; zero airflow)

Finite Element Method



A = 600 mm²; $T_a = 298$ K; $T_{max} = 353$ K



A = 300 mm²; $T_a = 298$ K; $T_{max} = 376$ K

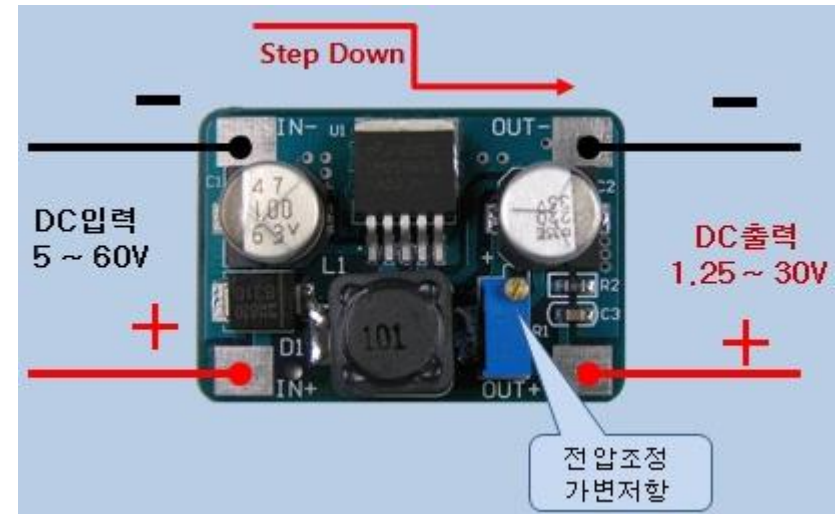
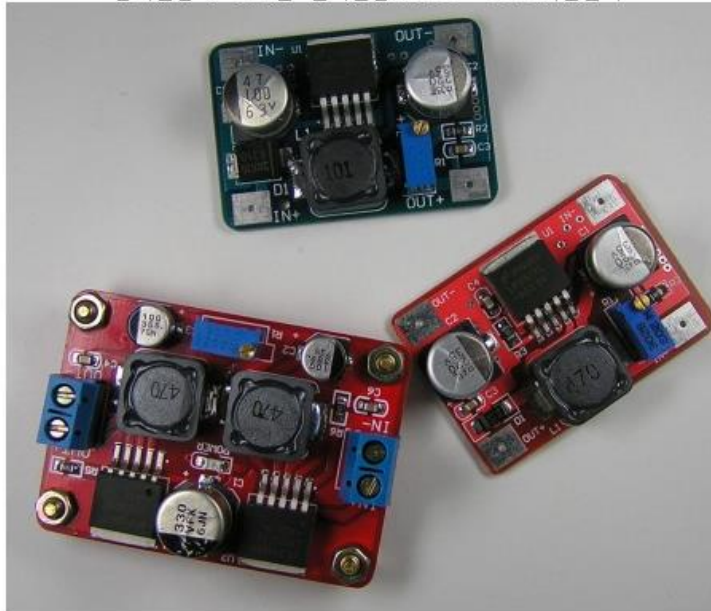


Footprint only; $T_a = 298$ K; $T_{max} = 442$ K

(option 3) DC/DC Module

전압강하형(Step Down) 가변 DCDC 모듈

입력전압 5~60V를 출력전압 1.25V ~ 26V 가변출력



○ 제품 설명

본 제품은 전압강하형(Step Down) DC/DC모듈로 입력전압 5~60V를 출력전압 1.25V~26V가변출력됩니다 실험용 소형 전원공급장치로 사용 가능합니다.

○ 제품 사양

- 작동 모드 : Step Down mode
- 입력전압 : 5V ~ 60V (권장 50V 이하)
- 출력전압 : 1.25V ~ 26V
- 출력전류 (연속출력) : 1.2A (총 20W 이내)
- 출력전류 (최대출력) : 3A
- 크기 : 43 x 30 x 13 mm (WHD)

<http://eleparts.co.kr/goods/view?no=31749>



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